



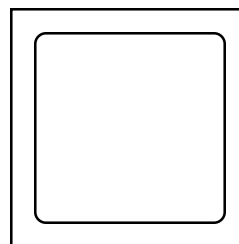
PRELIMINARY

SOLID STATE DEVICES, INC.14005 Stage Road * Santa Fe Springs, Ca 90670
Phone: (562) 404-4474 * Fax: (562) 404-1773**SEP0525****Designer's Data Sheet****FEATURES:**

- Low V_F , 300mV @ 1A, $T_J = 75^\circ\text{C}$
- Low Reverse Leakage Current
- Low Conduction Current (<100mV @ 1mA)
- Guard Ring for Overvoltage Protection
- 100°C Operating Temperature
- Solderable Top or Wire Bondable Metal Scheme Available

**5 AMPS
25 VOLTS
SUPER SCHOTTKY
RECTIFIER**

RECTIFIER DIE



Maximum Ratings	SYMBOL	VALUE	UNITS
Peak Repetitive Reverse and DC Blocking Voltage	V_R	25	Volts
Average Rectified Forward Current (Resistive Load, 60Hz, Sine Wave, $T_J = 75^\circ\text{C}$)	I_o	5	Amps
Operating and Storage Temperature	Top & Tstg	-55 TO +100	°C

NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: SH0006A

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Electrical Characteristics	SYMBOL	VALUE	UNITS
Instantaneous Forward Voltage Drop ($I_F = 5A_{DC}$, $T_J = 25^\circ C$, 300 μs Pulse)	V_{F1}	0.340	V_{DC}
Instantaneous Forward Voltage Drop ($I_F = 5A_{DC}$, $T_J = 75^\circ C$, 300 μs Pulse)	V_{F2}	0.300	V_{DC}
Reverse Leakage Current $T_J = 25^\circ C$, 300 μsec pulse minimum $V_R = 3.3V$ $V_R = 25V$	I_{R1} I_{R2}	4.0 10	mA mA
Reverse Leakage Current $T_J = 75^\circ C$, 300 μsec pulse minimum $V_R = 3.3V$ $V_R = 25V$	I_{R3} I_{R4}	30 100	mA mA
Reverse Leakage Current $T_J = 100^\circ C$, 300 μsec pulse minimum $V_R = 3.3V$ $V_R = 15V$	I_{R5} I_{R6}	75 200	mA mA
Junction Capacitance ($V_R = 5V_{DC}$, $T_J = 25^\circ C$, $f = 1MHz$)	C_J	800	pF

CASE OUTLINE:

